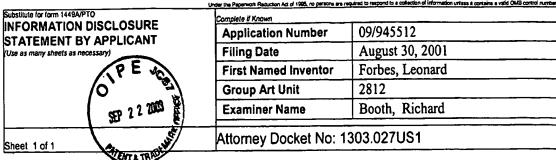
PRINTER RUSH (PTO ASSISTANCE) Examiner : Application: GAU: "IDC FMF FDC From: Location: ( Date: Tracking #: Week Date: **DOC**CODE **DOC DATE MISCELLANEOUS** 1449 Continuing Data √ IDS Foreign Priority **CLM Document Legibility IIFW** Fees **SRFW** Other **DRW OATH** 312 **SPEC** [RUSH] MESSAGE: [XRUSH] **RESPONSE**:

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.

REV 10/04

**INITIALS:** 



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